

All Purpose InGaAs p-i-n Photodiode

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35PD300LDC-ST, -SMA, -FC, -SC

The 35PD300LDC-ST, an InGaAs photodiode with a 300 μ m-diameter photosensitive region packaged in a TO-46 header and actively aligned in a AT&T ST active device mount, is a low-dark-current version of the 35PD300. This device is one of Telcom Devices' most versatile optoelectronic components designed for applications in high sensitivity instrumentation, and moderate-bit-rate fiberoptic communications. Planar semiconductor design and dielectric passivation provide superior performance. Reliability is assured by hermetic sealing and 100% purge burn-in (200°C, 15 hours, Vr = 20V). Devices with enhanced responsivity at 850 nm are available.



Features:

- Planar Structure
- Dielectric Passivation
- 100% Purge Burn-in
- High Responsivity

DEVICE CHARACTERISTICS

Parameters	Test Conditions	Minimum	Typical	Maximum	Units
Operating Voltage				-15	Volts
Dark Current	-5V			0.51	nA
Capacitance	-5V		4	12	pF
Responsivity	1300nm	0.7	0.9		A/W
Responsivity				3	ns
Rise/Fall	(-3dB)		300		GHz

ABSOLUTE MAXIMUM RATINGS

Reverse Voltage	20 Volts
Forward Current	25mA
Reverse Current	5mA
Operating Temperature	-40°C to +85°C
Storage Temperature	-40°C to +85°C
Soldering Temperature	250°C

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829 Flynn Road, Camarillo, CA 93012 • Phone: (805) 445-4500 • Fax: (805) 445-4502
Email: customerservice@telcomdevices.com • Website: www.telcomdevices.com



Telcom Devices Corp.